

Compound Devices

NPN Dual Transistors in 6 lead TO5 Encapsulation

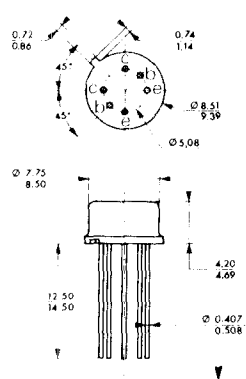
Type	Maximum ratings			Characteristics at T _{amb} = 25°C			
	BV _{CEO} V	I _{CM} mA	P _{tot} ¹ W	h _{FE} (V _{CE} /I _C) (V/uA)	h _{FE1} /h _{FE2}	V _{BE1} -V _{BE2} mV	f _T MHz
NKT 6003	40	30	0.15	100 (5/10)	0.83 ... 1.2	±3.0	50
NKT 6010	40	30	0.15	100 (5/10)	0.83 ... 1.2	±10.0	50

¹ T_{amb} = 25°C

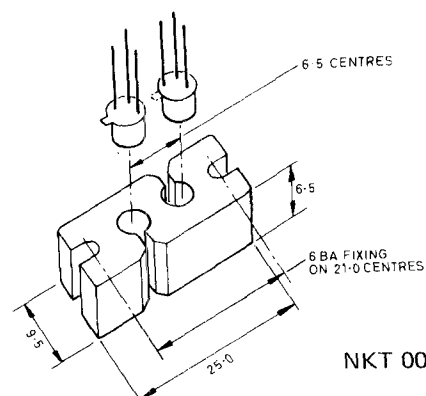
Differential Amplifier Pairs – NPN

Type	Maximum ratings			Characteristics at T _{amb} = 25°C					
	BV _{CEO} V	BV _{EBO} V	I _{CM} mA	P _{tot} ¹ W	h _{FE} (V _{CE} V, I _C uA)	V _{BE} (V _{CB} /I _E) V (V/mA)	h _{FE1} /h _{FE2}	V _{BE1} –V _{BE2} mV	
BCY 55	45	5	30	0.3	> 100 (5,100)	0.6 ... 0.8 (5/0.5)	0.85 ... 1.18	±4.0	
NKT 0055	45	5	30	0.3	> 100 (5,100)	—	0.91 ... 1.11	±3.0	

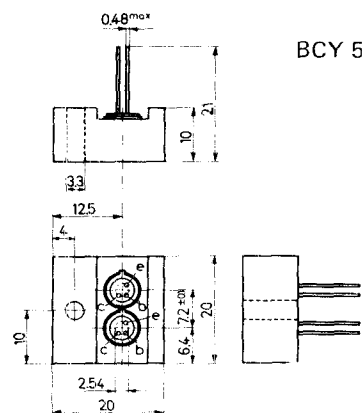
¹ T_{amb} = 25°C



Dual Transistor



NKT 0055



BCY 55